

10. (Three Times Amended) An ohmic electrode obtained by annealing a multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, a TiSiN film, and a TiON film.

19. (Three Times Amended) An ohmic electrode provided on a III-V compound semiconductor body obtained by annealing a multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprised of In and a film including at least a metal nitride film,

the energy barrier between said non-single crystal semiconductor layer and said film being lower than the energy barrier between said III-V compound semiconductor body and said film, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, a TiSiN film, and a TiON film.